

Abstract

CROSS-POINT MEMORY AND METHODS FOR FABRICATION OF SAME

The disclosed technology relates generally to integrated circuit devices, and in particular to cross-point memory arrays and methods for fabricating the same, in one aspect, a method of fabricating cross-point memory arrays comprises forming a memory cell material stack which includes a first active material and a second active material over the first active material, wherein one of the first and second active materials comprises a storage material and the other of the first and second active materials comprises a selector material. The method of fabricating cross-point arrays further comprises patterning the memory cell material stack, which includes etching through at least one of the first and second active materials of the memory cell material stack, forming protective liners on sidewalls of the at least one of the first and second active materials after etching through the one of the first and second active materials, and further etching the memory cell material stack after forming the protective liners on the sidewalls of the one of the first and second active materials.

Figure 2N